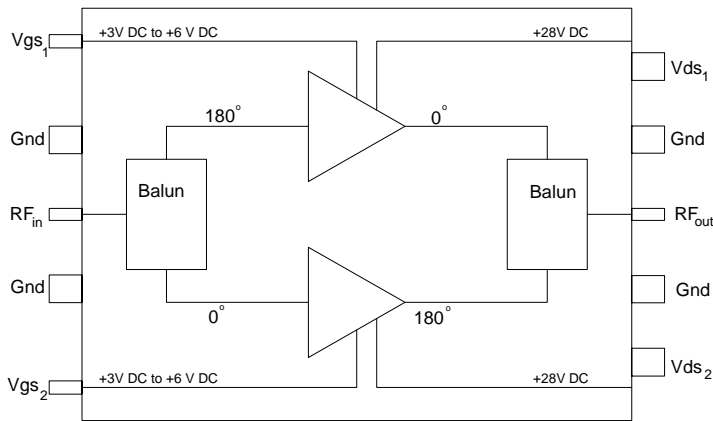




Product Description

Sirenza Microdevices' **SDM-08060-B1F** 65W power module is a robust, impedance matched, single-stage, push-pull Class AB amplifier module suitable for use as a power amplifier driver or output stage. The power transistors are fabricated using Sirenza's latest, high performance LDMOS process. It is a drop-in, no-tune solution for high power applications requiring high efficiency, excellent linearity, and unit-to-unit repeatability. It is internally matched to 50 ohms.

Functional Block Diagram

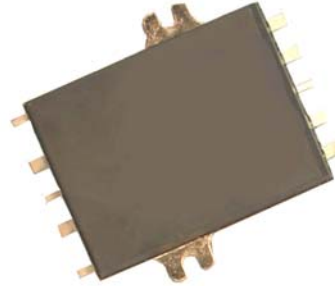


Case Flange = Ground

SDM-08060-B1F SDM-08060-B1FY



**869-894 MHz Class AB
65W Power Amplifier Module**



Product Features

- Available in RoHS compliant packaging
- 50 Ω RF impedance
- 65W Output P_{1dB}
- Single Supply Operation : Nominally 28V
- High Gain: 17 dB at 880 MHz
- High Efficiency: 46% at 880 MHz
- ESD Protection: JEDEC Class 2 (2000V HBM)

Applications

- Base Station PA driver
- Repeater
- CDMA
- GSM / EDGE

Key Specifications

Symbol	Parameter	Units	Min.	Typ.	Max.
Frequency	Frequency of Operation	MHz	869	-	894
P_{1dB}	Output Power at 1dB Compression, 881 MHz	W	60	65	-
Gain	Gain at 12W CDMA Output (Single Carrier IS-95), 881MHz	dB	16	17	-
Gain Flatness	Peak to Peak Gain Variation, 869 - 894MHz	dB	-	0.3	0.5
Efficiency	Drain Efficiency at 60W PEP, 880MHz and 881MHz	%	32	34	-
Efficiency	Drain Efficiency at 60W CW, 880MHz	%	-	46	-
IRL	Input Return Loss 12W CW Output Power, 869 - 894MHz	dB	-	-15	-10
IMD	3rd Order IMD Product, 60W PEP, 880MHz and 881MHz	dBc	-	-31	-28
Delay	Signal Delay from Pin 3 to Pin 8	nS	-	4.0	-
Phase Linearity	Deviation from Linear Phase (Peak to Peak)	Deg	-	0.5	-
R_{TH}	Thermal Resistance (Junction to Case)	$^{\circ}C/W$	-	1.5	-

Test Conditions $Z_{in} = Z_{out} = 50\Omega$, $V_{DD} = 28.0V$, $I_{DQ1} = I_{DQ2} = 300mA$, $T_{Flange} = 25^{\circ}C$

Quality Specifications

Parameter	Description	Unit	Typical
ESD Rating	Human Body Model	Volts	2000
MTTF	200 $^{\circ}C$ Channel	Hours	1.2 X 10 ⁶

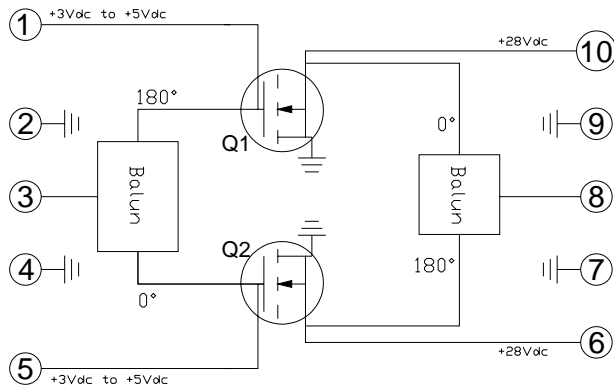
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303 S. Technology Court, Broomfield, CO 80021 Phone: (800) SMI-MMIC <http://www.sirenza.com>
EDS-104208 Rev F

Pin Description

Pin #	Function	Description
1	V _{GS1}	LDMOS FET Q1 gate bias. V _{GSTH} 3.0 to 5.0 VDC. See Notes 2, 3 and 4
2,4,7,9	Ground	Module Topside ground.
3	RF Input	Internally DC blocked
5	V _{GS2}	LDMOS FET Q2 gate bias. V _{GSTH} 3.0 to 5.0 VDC. See Notes 2, 3 and 4
6	V _{D2}	LDMOS FET Q2 drain bias. See Note 1.
8	RF Output	Internally DC blocked
10	V _{D1}	LDMOS FET Q1 drain bias. See Note 1.
Flange	Ground	Baseplate provides electrical ground and a thermal transfer path for the device. Proper mounting assures optimal performance and the highest reliability. See Sirenza applications note AN-054 Detailed Installation Instructions for Power Modules.

Simplified Device Schematic



Case Flange = Ground

Absolute Maximum Ratings

Parameters	Value	Unit
Drain Voltage (V _{DD})	35	V
RF Input Power	+37	dBm
Load Impedance for Continuous Operation Without Damage	5:1	VSWR
Control (Gate) Voltage, V _{DD} = 0 VDC	15	V
Output Device Channel Temperature	+200	°C
Operating Temperature Range	-20 to +90	°C
Storage Temperature Range	-40 to +100	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation see typical setup values specified in the table on page one.

Note 1:

Internal RF decoupling is included on all bias leads. No additional bypass elements are required, however some applications may require energy storage on the V_D leads to accommodate modulated signals.

Note 2:

Gate voltage must be applied to V_{GS} leads simultaneously with or after application of drain voltage to prevent potentially destructive oscillations. Bias voltages should never be applied to a module unless it is properly terminated on both input and output.

Note 3:

The required V_{GS} corresponding to a specific I_{DQ} will vary from module to module and may differ between V_{GS1} and V_{GS2} on the same module by as much as ±0.10 volts due to the normal die-to-die variation in threshold voltage. LDMOS transistors.

Note 4:

The threshold voltage (V_{GSTH}) of LDMOS transistors varies with device temperature. External temperature compensation may be required. See Sirenza application notes AN-067 LDMOS Bias Temperature Compensation.

Note 5:

This module was designed to have its leads hand soldered to an adjacent PCB. The maximum soldering iron tip temperature should not exceed 700° F, and the soldering iron tip should not be in direct contact with the lead for longer than 10 seconds. Refer to app note AN054 (www.sirenza.com) for further installation instructions.

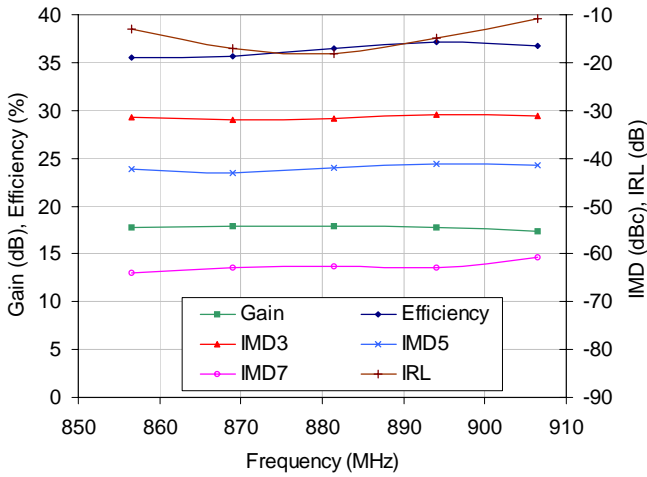


Caution: ESD Sensitive

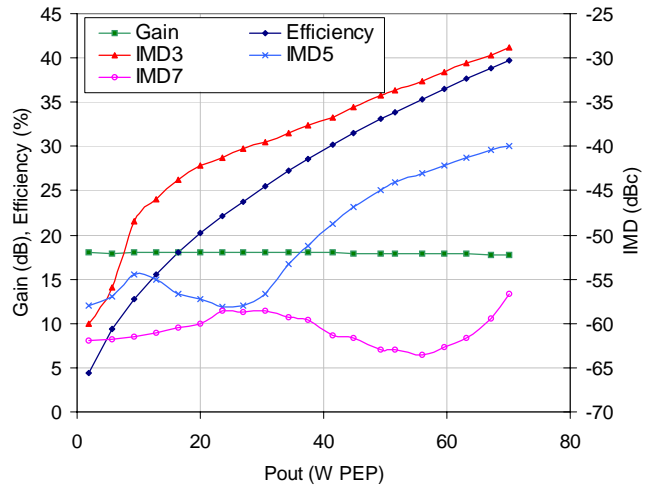
Appropriate precaution in handling, packaging and testing devices must be observed.

Typical Performance Curves

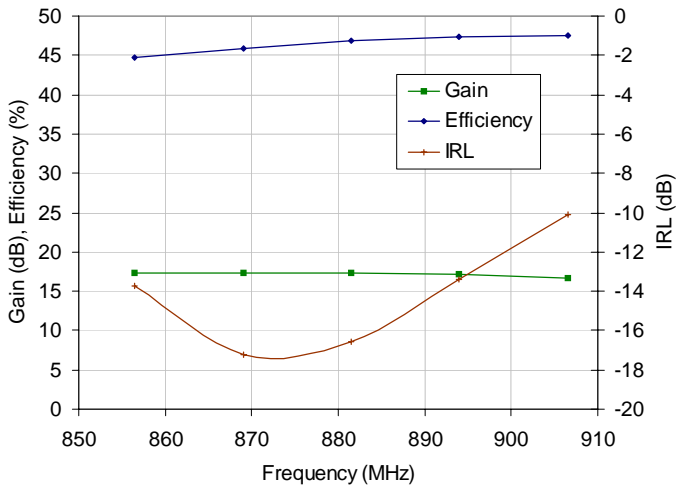
2 Tone Gain, Efficiency, IMDs, IRL vs Frequency
 Vdd=28V, Idq=600mA, Pout=60W PEP, Delta F=1 MHz



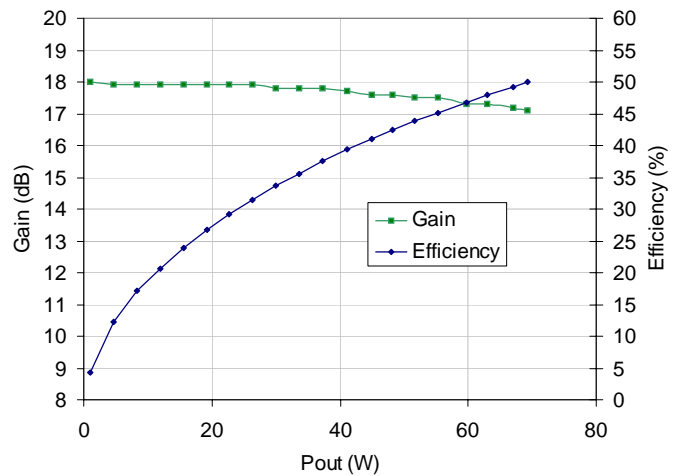
2 Tone Gain, Efficiency, IMDs vs Pout
 Vdd=28V, Idq=600mA, Freq=881 MHz, Delta F=1 MHz



CW Gain, Efficiency, IRL vs Frequency
 Vdd=28V, Idq=600mA, Pout=60W

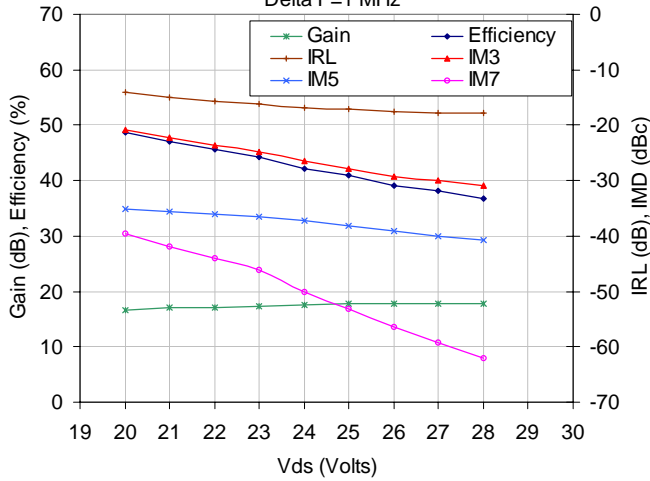


CW Gain, Efficiency vs Pout
 Vdd=28V, Idq=600mA, Freq=881 MHz

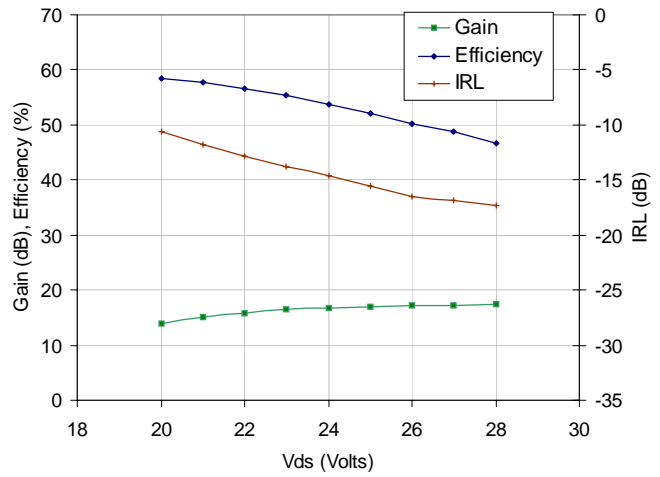


Typical Performance Curves (cont'd)

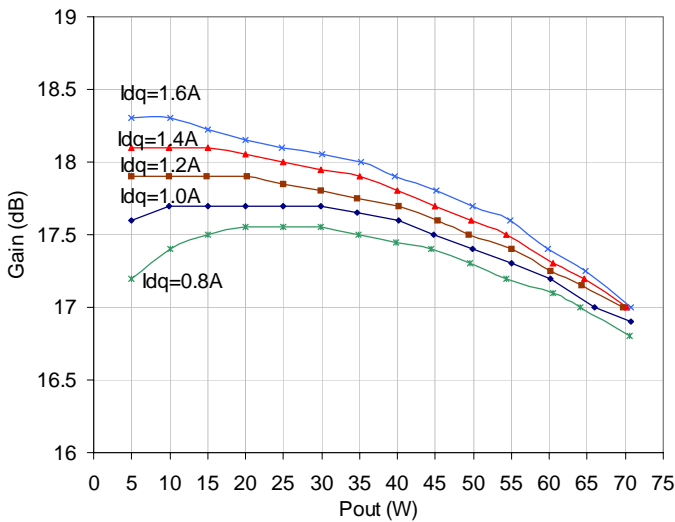
Two Tone Gain, Efficiency, IRL, IMDs vs Supply Voltage
 Pout=60W PEP, Idq=600mA, Freq=881 MHz,
 Delta F=1 MHz



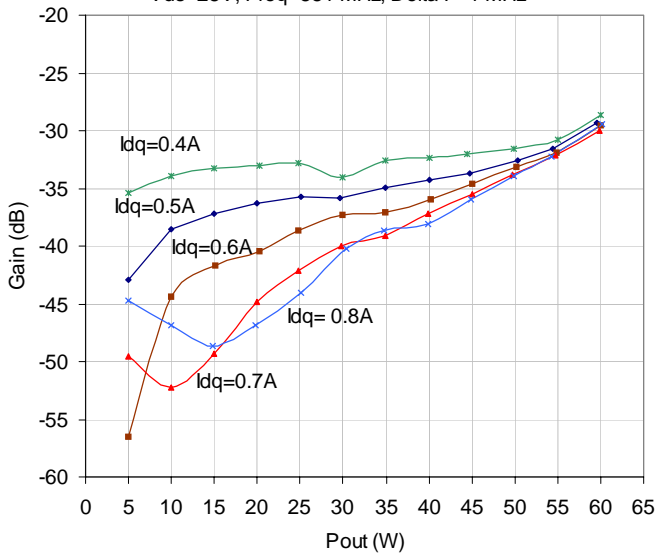
CW Gain, Efficiency, IRL vs Supply Voltage
 Pout=60W, Idq=600mA, Freq=881 MHz



CW Gain vs Pout for various Idq
 Vds=28V, Freq=881 MHz



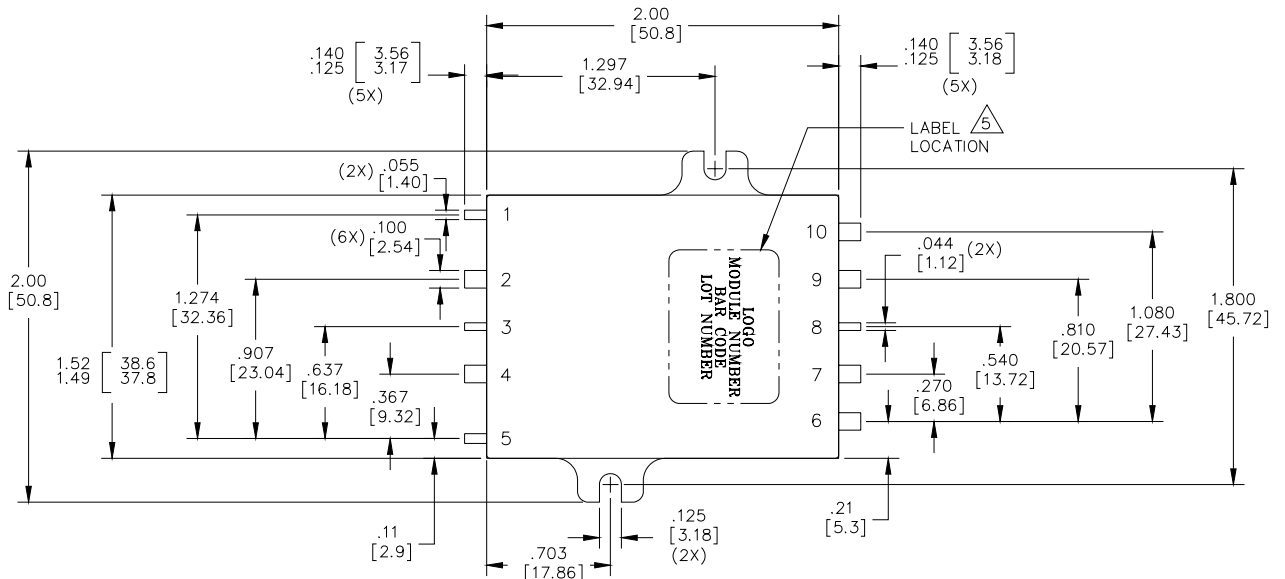
IMD3 vs Pout for various Idq
 Vds=28V, Freq=881 MHz, Delta F=1 MHz



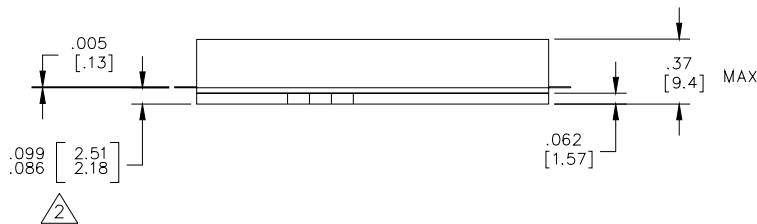
Note:

Evaluation test fixture information available on Sirenza Website, referred to as SDM-EVAL.

Package Outline Drawing



LEAD IDENTIFICATION	
Lead No.	Function
1	Bias 1
2	Ground
3	Input
4	Ground
5	Bias 2
6	V _{DD2}
7	Ground
8	Output
9	Ground
10	V _{DD1}
BASE PLATE	Ground



MODULE WEIGHT = 43gm NOMINAL

NOTES: UNLESS OTHERWISE SPECIFIED

1. INTERPRET DRAWING PER ANSI Y14.5..
2. MEASURE FROM THE BOTTOM OF THE LEADS.
3. DIMENSIONS ARE INCHES[MM].
4. LEAD IDENTIFICATION IS FOR REFERENCE ONLY.
5. ORIENTATION OF LABEL IS TO BE AS SHOWN.

Note:

Refer to Application note AN054, "Detailed Installation Instructions for Power Modules" for detailed mounting information.